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[METHOD FOR FABRICATING FLASH MEMORY]

Abstract of Disclosure

A method for fabricating a flash memory is described. A stacked gate structure and a source/drain are formed on a substrate. An inter-layer dielectrics and a plurality of inter-metal dielectric layers are then formed over the substrate, wherein at least one layer among the inter-layer dielectrics and the inter-metal dielectric layers has a silicon carbide layer formed thereon. The silicon carbide layer is formed to protect the memory device from an UV irradiation, so as to prevent data errors occurring in the memory device.

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